

AMENDMENTS TO THE CLAIMS

This Listing of Claims will replace all prior versions, listing, of claims in the specification.

LISTING OF CLAIMS:

Claim 1 (original) An epitaxial structure of GaN based compound semiconductor comprising:

a substrate;

a single crystal of boron phosphide buffer layer on said substrate;

a first buffer layer composed of group III nitride at a temperature from 200 to 800 degree C formed on said boron phosphide buffer layer; and

a second buffer layer composed of group III nitride at a temperature from 800 to 1100 degree C formed on said first buffer layer.

Claim 2 (original) The epitaxial structure of GaN based compound semiconductor of claim 1, wherein said substrate is a single crystal silicon.

Claim 3 (original) The epitaxial structure of GaN based compound semiconductor of claim 1, wherein said boron phosphide buffer layer comprises a first layer formed at a temperature from 300 to 850 degree C and a second layer formed at a temperature from 800 to 1100 degree C.

Claim 4 (original) The epitaxial structure of GaN based compound semiconductor of claim 1, wherein said first and second buffer layer are composed of  $\text{Al}_x\text{In}_y\text{Ga}_z\text{N}$ , wherein  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  $0 \leq z \leq 1$ ,  $x+y+z=1$ .

Claim 5 (original) The epitaxial structure of GaN based compound semiconductor of claim 1, wherein said first and second buffer layer are composed of  $\text{In}_x\text{Ga}_y\text{N}_z\text{P}$ , wherein  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  $0 \leq z \leq 1$ ,  $x+y+z=1$ .

Claims 6-10 (canceled).